



TAYCHIPST Surface Mount Trench MOS Barrier Schottky Rectifier

VSSB310

100V 3.0A

FEATURES

- Low profile package
- Ideal for automated placement
- Trench MOS Schottky technology
- Low power losses, high efficiency
- Low forward voltage drop
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

Mechanical Data

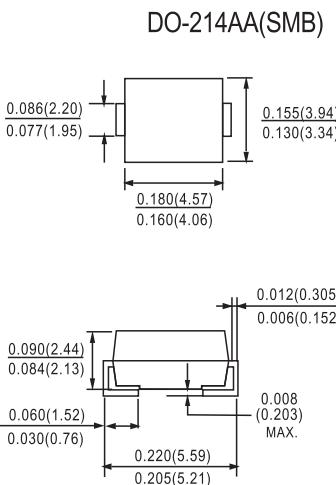
Case: DO-214AA (SMB)

Molding compound meets UL 94 V-0 flammability rating
Base P/N-E3 - RoHS compliant, commercial grade

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

E3 suffix meets JESD 201 class 1A whisker test

Polarity: Color band denotes the cathode end



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	VSSB310	UNIT
Device marking code		V3B	
Maximum repetitive peak reverse voltage	V _{RRM}	100	V
Maximum DC forward current	I _F ⁽¹⁾	3.0	A
	I _F ⁽²⁾	1.9	
Peak forward surge current 10 ms single half sine-wave superimposed on rated load	I _{FSM}	80	A
Non-repetitive avalanche energy at $T_J = 25^\circ\text{C}$, $L = 60 \mu\text{H}$	E _{AS}	50	mJ
Peak repetitive reverse current at $t_p = 2 \mu\text{s}$, 1 kHz, $T_J = 38^\circ\text{C} \pm 2^\circ\text{C}$	I _{RRM}	1.0	A
Operating junction and storage temperature range	T _J , T _{STG}	- 40 to + 150	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER	TEST CONDITIONS	SYMBOL	TYP.	MAX.	UNIT
Breakdown voltage	I _R = 1.0 mA	V _{BR}	100 (minimum)	-	V
Instantaneous forward voltage	I _F = 3.0 A	V _F ⁽¹⁾	0.62	0.70	V
			0.56	0.65	
Reverse current	V _R = 70 V	I _R ⁽²⁾	1.5	-	μA
			1.2	-	mA
	V _R = 100 V		7.0	250	μA
			3.6	20	mA
Typical junction capacitance	4.0 V, 1 MHz	C _J	230	-	pF

THERMAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	VSSB310	UNIT
Typical thermal resistance	R _{θJA} ⁽¹⁾	120	°C/W
	R _{θJM} ⁽²⁾	15	

Notes

⁽¹⁾ Free air, mounted on recommended P.C.B. 1 oz. pad area. Thermal resistance R_{θJA} - junction to ambient

⁽²⁾ Units mounted on P.C.B. with 10 mm x 10 mm copper pad areas. R_{θJM} - junction to mount



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RATINGS AND CHARACTERISTIC CURVES VSSB310

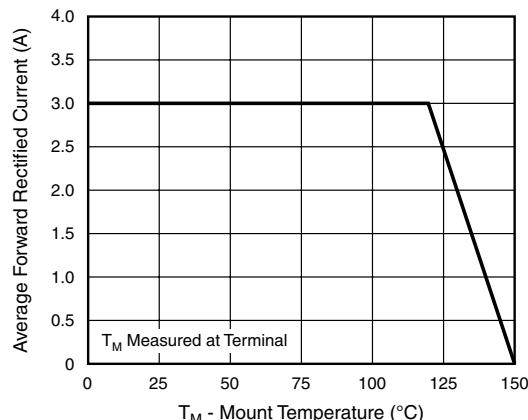


Fig. 1 - Maximum Forward Current Derating Curve

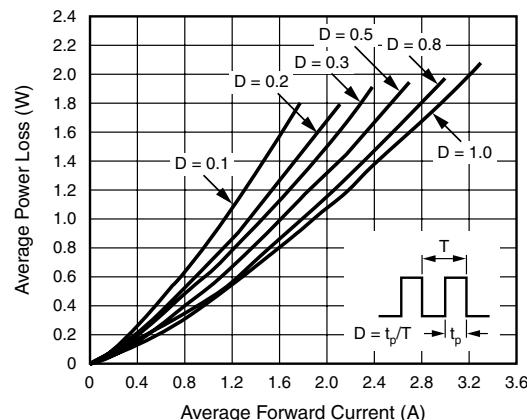


Fig. 2 - Forward Power Loss Characteristics

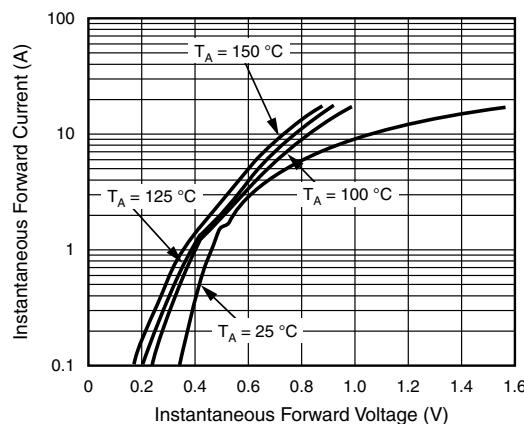


Fig. 3 - Typical Instantaneous Forward Characteristics

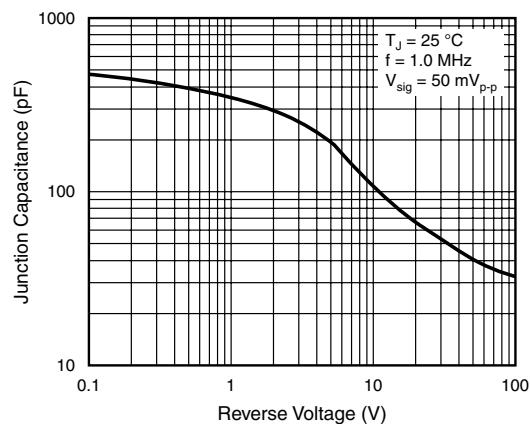


Fig. 5 - Typical Junction Capacitance

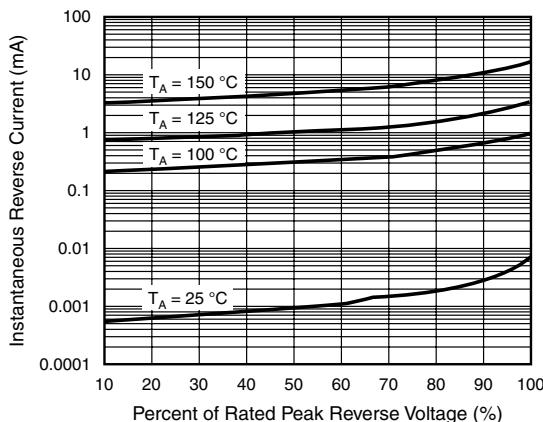


Fig. 4 - Typical Reverse Characteristics

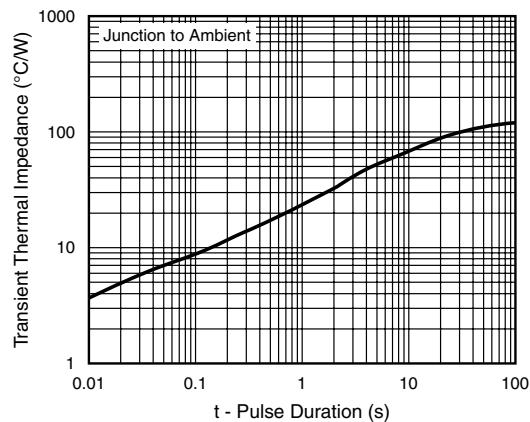


Fig. 6 - Typical Transient Thermal Impedance